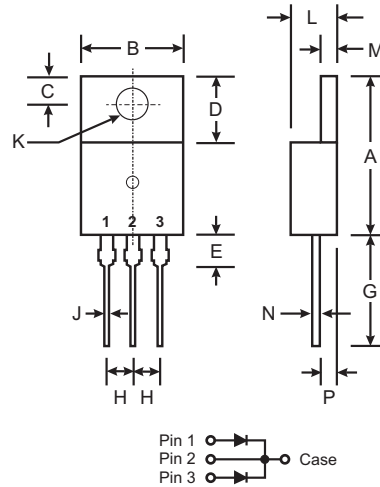


### Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- **Lead Free Finish, RoHS Compliant (Note 3)**

### Mechanical Data

- Case: TO-220AB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Polarity: As Marked on Body
- Terminals: Finish – Bright Tin. Solderable per MIL-STD-202, Method 208
- Mounting Position: Any
- Marking: Type Number
- Weight: 2.24 grams (approx)



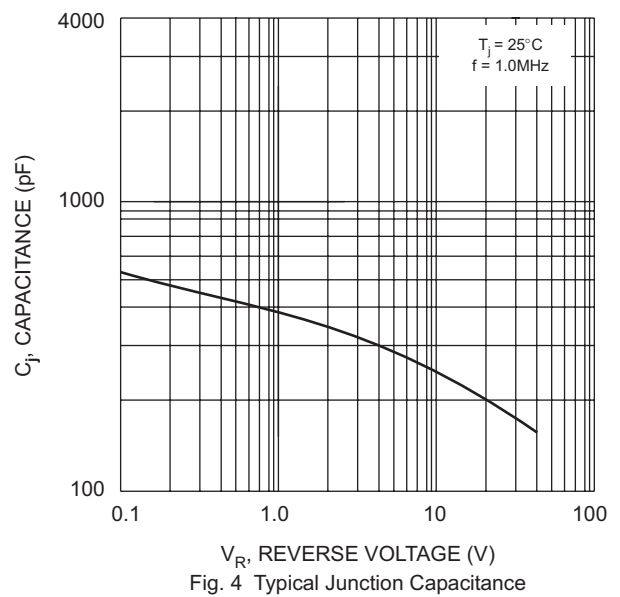
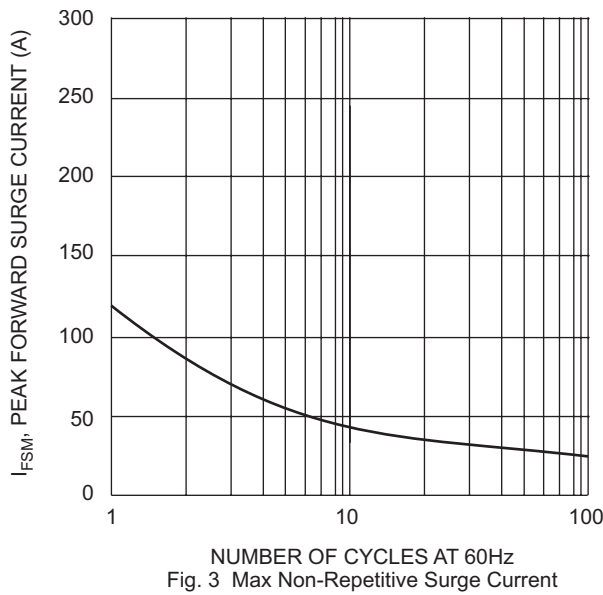
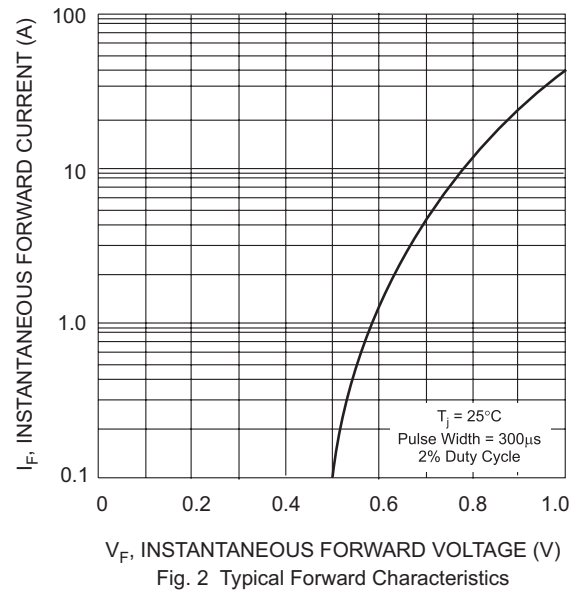
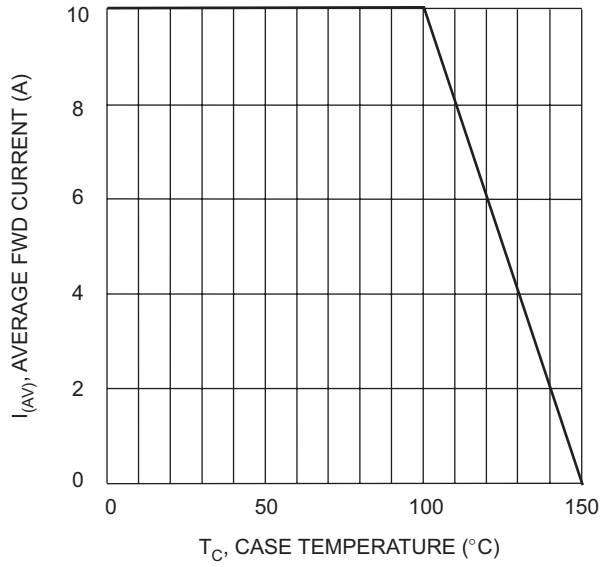
TO-220AB		
Dim	Min	Max
A	14.48	15.75
B	10.00	10.40
C	2.54	3.43
D	5.90	6.40
E	2.80	3.93
G	12.70	14.27
H	2.40	2.70
J	0.69	0.93
K	3.54	3.78
L	4.07	4.82
M	1.15	1.39
N	0.30	0.50
P	2.04	2.79
All Dimensions in mm		

### Maximum Ratings and Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1070CT	MBR 1080CT	MBR 1090CT	MBR 10100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	70	80	90	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	49	56	63	70	V
Average Rectified Output Current (Note 1) @ T <sub>C</sub> = 100°C	I <sub>O</sub>	10				A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	120				A
Forward Voltage Drop @ I <sub>F</sub> = 5.0A, T <sub>C</sub> = 125°C @ I <sub>F</sub> = 5.0A, T <sub>C</sub> = 25°C @ I <sub>F</sub> = 10A, T <sub>C</sub> = 125°C @ I <sub>F</sub> = 10A, T <sub>C</sub> = 25°C	V <sub>FM</sub>	0.75 0.85 0.85 0.95				V
Peak Reverse Current at Rated DC Blocking Voltage @ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 125°C	I <sub>RM</sub>	0.1 50				mA
Typical Junction Capacitance (Note 2)	C <sub>j</sub>	300				pF
Typical Thermal Resistance Junction to Case (Note 1)	R <sub>θJC</sub>	3.0				K/W
Voltage Rate of Change	dV/dt	10,000				V/μs
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150				°C

- Notes:
1. Thermal resistance junction to case mounted on heatsink.
  2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
  3. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see EU Directive Annex Notes 5 and 7.



**Ordering Information** (Note 4)

Device	Packaging	Shipping
MBR10xxCT*	TO-220AB	50/Tube

\* xx = Device type, e.g. MBR1080CT

Notes: 4. For packaging details, visit our website at <http://www.diodes.com/datasheets/ap02008.pdf>.